HAT2038R/HAT2038RJ

Silicon N Channel Power MOS FET
High Speed Power Switching

HITACHI

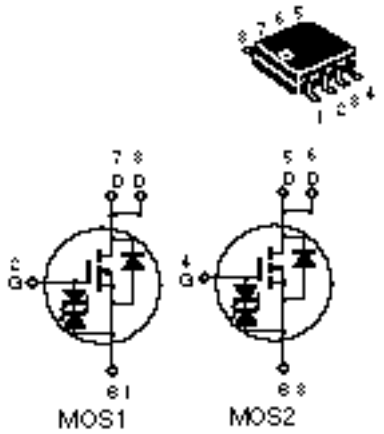
ADE-208-666C (Z)
4th. Edition
February 1999

Features

- For Automotive Application (at Type Code “J “)
- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

Outline

SOP-8



1, 3	Source
2, 4	Gate
5, 6, 7, 8	Drain

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage		V_{DSS}	60	V
Gate to source voltage		V_{GSS}	±20	V
Drain current		I_D	5	A
Drain peak current		$I_{D(pulse)}$ Note1	40	A
Body-drain diode reverse drain current		I_{DR}	5	A
Avalanche current	HAT2038R	I_{AP} Note4	—	—
	HAT2038RJ		5	A
Avalanche energy	HAT2038R	E_{AR} Note4	—	—
	HAT2038RJ		2.14	mJ
Channel dissipation		Pch Note2	2	W
Channel dissipation		Pch Note3	3	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	–55 to +150	°C

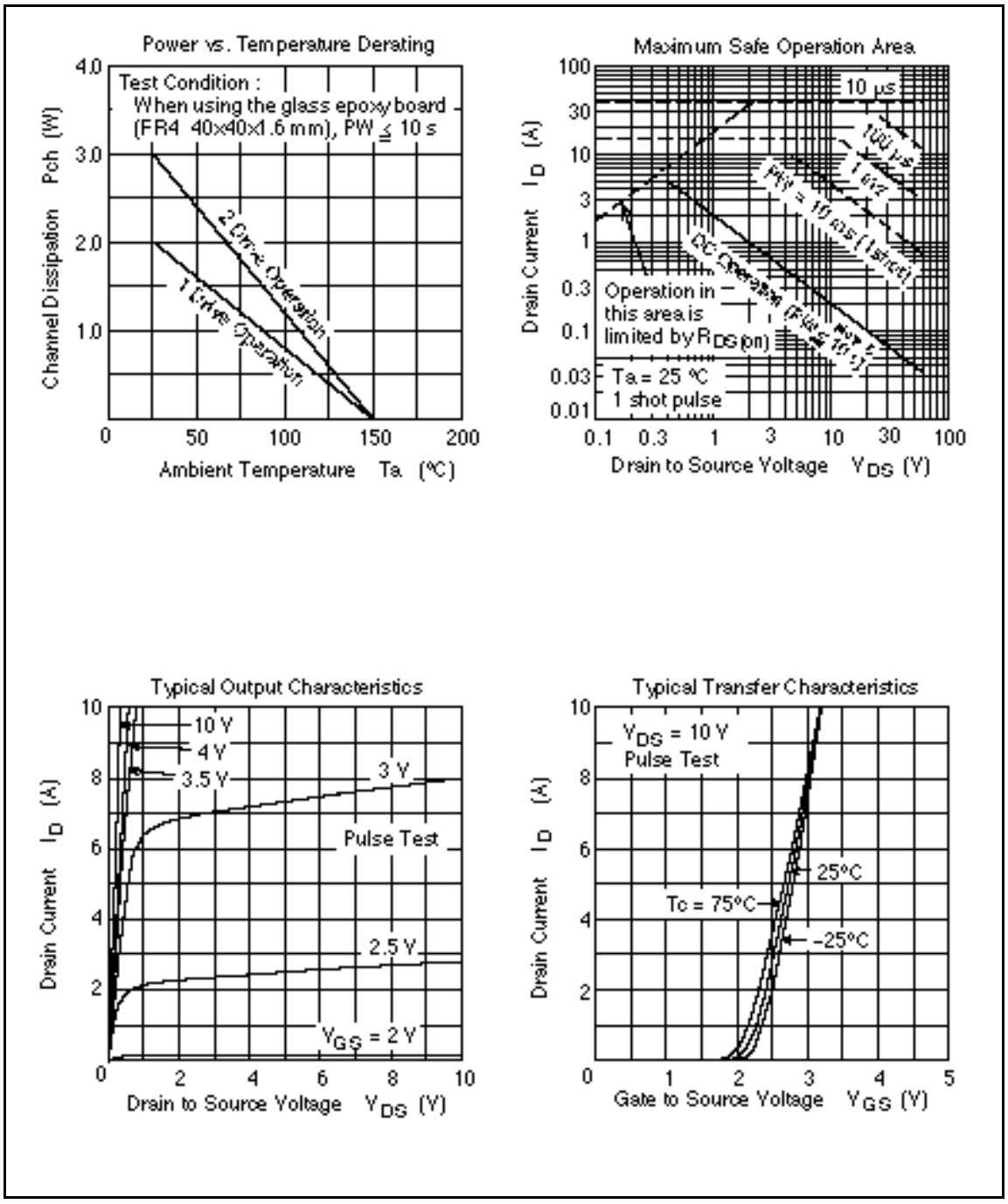
Note: 1. PW ≤ 10µs, duty cycle ≤ 1 %
2. 1 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10s
3. 2 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10s
4. Value at Tch=25°C, Rg ≥ 50Ω

Electrical Characteristics (Ta = 25°C)

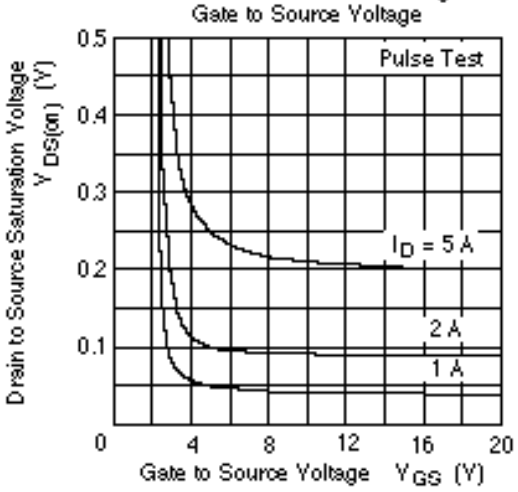
Item		Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage		$V_{(BR)DSS}$	60	—	—	V	I_D = 10mA, V_{GS} = 0
Gate to source breakdown voltage		$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100µA, V_{DS} = 0
Gate to source leak current		I_{GSS}	—	—	±10	µA	V_{GS} = ±16V, V_{DS} = 0
Zero gate voltage	HAT2038R	I_{DSS}	—	—	1	µA	V_{DS} = 60V, V_{GS} = 0
drain current	HAT2038RJ	I_{DSS}	—	—	0.1	µA	
Zero gate voltage	HAT2038R	I_{DSS}	—	—	—	µA	V_{DS} =48V, V_{GS} = 0
drain current	HAT2038RJ	I_{DSS}	—	—	10	µA	Ta=125°C
Gate to source cutoff voltage		$V_{GS(off)}$	1.2	—	2.2	V	V_{DS} = 10V, I_D = 1mA
Static drain to source on state resistance		$R_{DS(on)}$	—	0.043	0.058	Ω	I_D = 3A, V_{GS} = 10V Note5
		$R_{DS(on)}$	—	0.056	0.084	Ω	I_D = 3A, V_{GS} = 4V Note5
Forward transfer admittance		$\|y_{fs}\|$	6	9	—	S	I_D = 3A, V_{DS} = 10V Note5
Input capacitance		Ciss	—	520	—	pF	V_{DS} = 10V
Output capacitance		Coss	—	270	—	pF	V_{GS} = 0
Reverse transfer capacitance		Crss	—	100	—	pF	f = 1MHz
Turn-on delay time		$t_{d(on)}$	—	11	—	ns	V_{GS} =10V, I_D = 3A
Rise time		t_r	—	40	—	ns	V_{DD} ≈ 30V
Turn-off delay time		$t_{d(off)}$	—	110	—	ns	
Fall time		t_f	—	80	—	ns	
Body–drain diode forward voltage		V_{DF}	—	0.84	1.1	V	IF = 5A, V_{GS} = 0 Note5
Body–drain diode reverse recovery time		t_{rr}	—	40	—	ns	IF =5A, V_{GS} = 0 diF/ dt =50A/µs

Note: 5. Pulse test

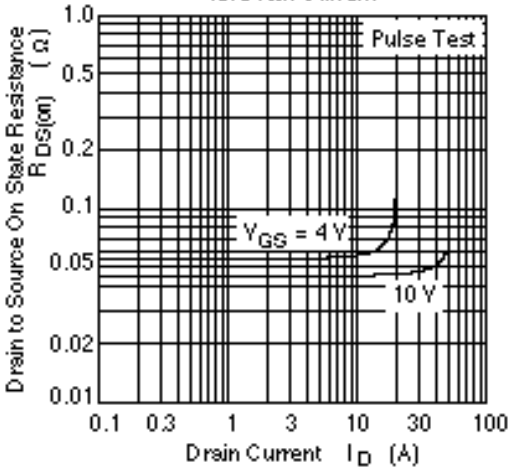
Main Characteristics



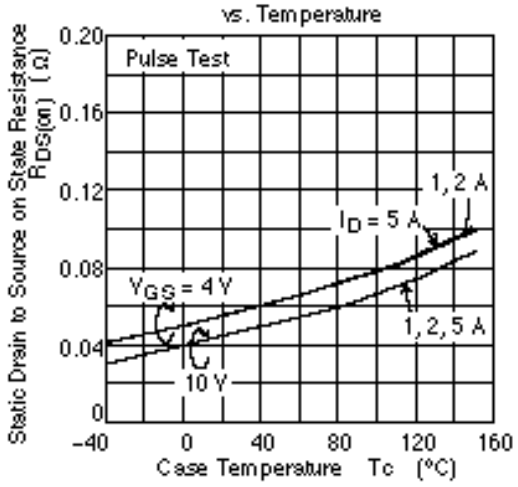
Drain to Source Saturation Voltage vs. Gate to Source Voltage



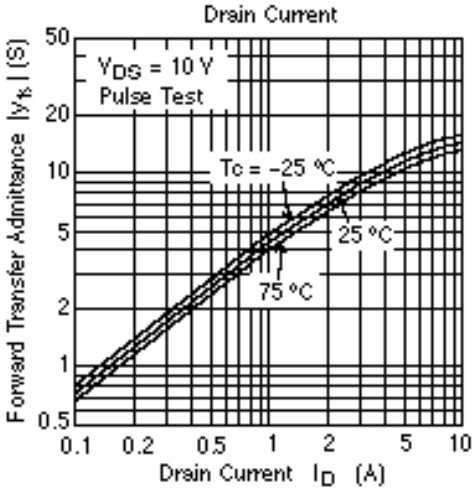
Static Drain to Source on State Resistance vs. Drain Current

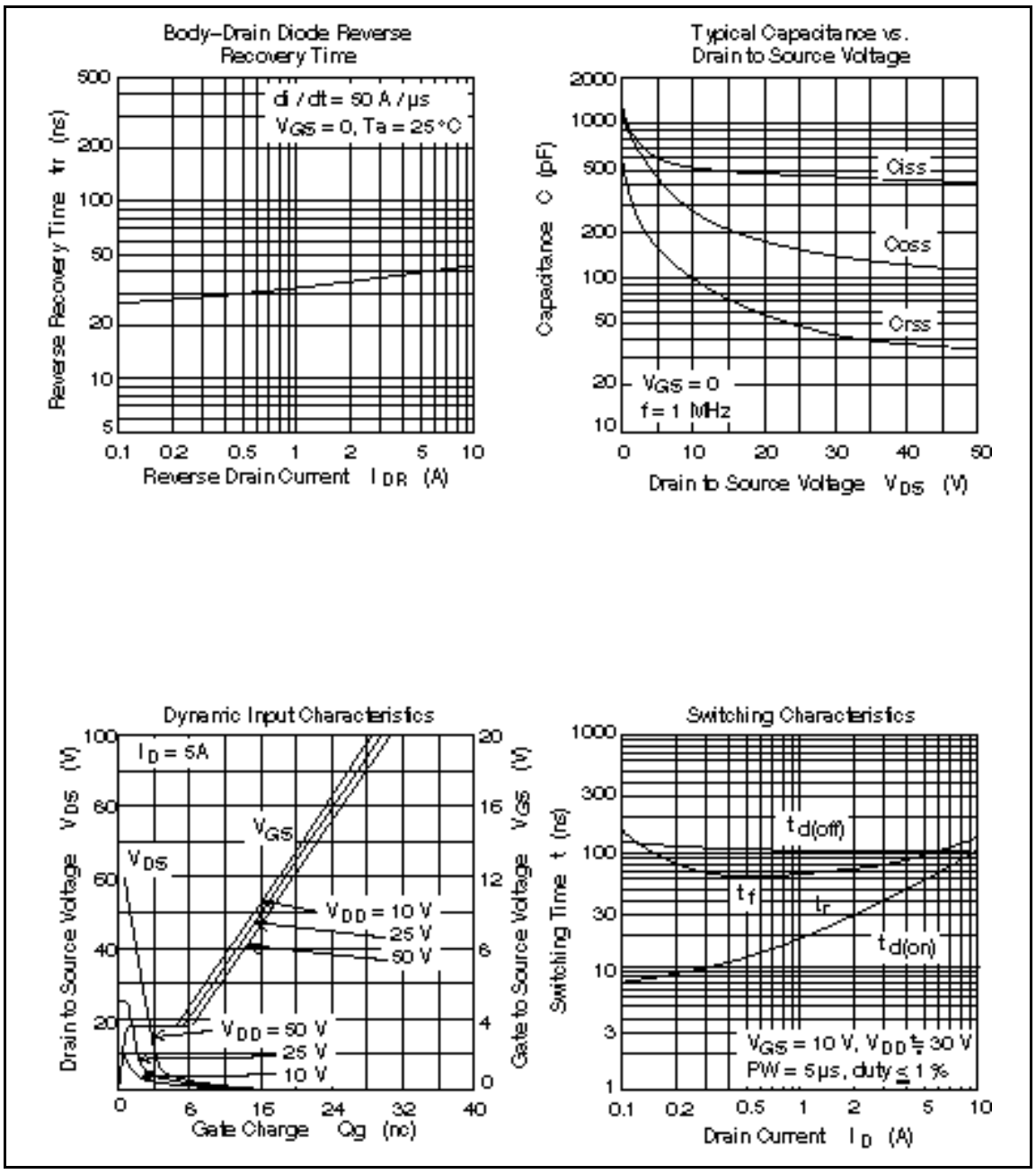


Static Drain to Source on State Resistance vs. Temperature

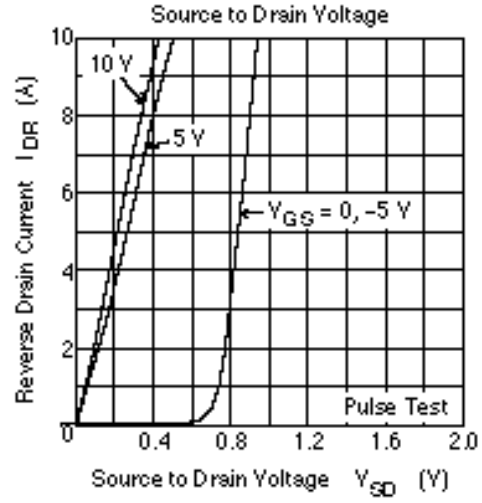


Forward Transfer Admittance vs. Drain Current

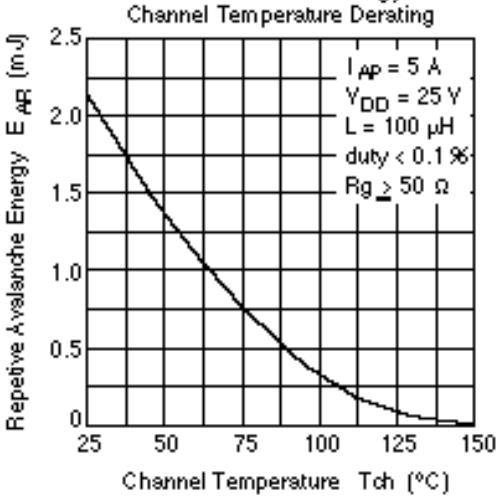



Body–Drain Diode Reverse Recovery Time
di / dt = 50 A / µs
VGS = 0, Ta = 25 °C
Reverse Recovery Time trr (ns)
Reverse Drain Current IDR (A)
Typical Capacitance vs. Drain to Source Voltage
Ciss
Coss
Crss
VGS = 0
f = 1 MHz
Capacitance C (pF)
Drain to Source Voltage VDS (V)
Dynamic Input Characteristics
ID = 5A
VGS
VDS
VDD = 10 V
25 V
50 V
VDD = 50 V
25 V
10 V
Drain to Source Voltage VDS (V)
Gate to Source Voltage VGS (V)
Gate Charge Qg (nc)
Switching Characteristics
td(off)
tf
tr
td(on)
VGS = 10 V, VDD ≒ 30 V
PW = 5 µs, duty ≦ 1 %
Switching Time t (ns)
Drain Current ID (A)

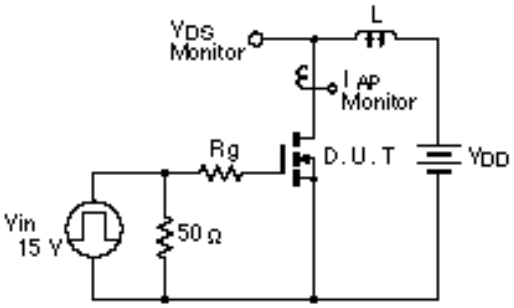
Reverse Drain Current vs. Source to Drain Voltage



Maximun Avalanche Energy vs. Channel Temperature Derating

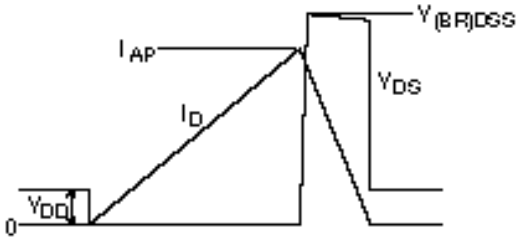


Avalanche Test Circuit

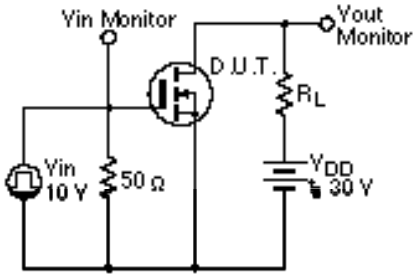


Avalanche Waveform

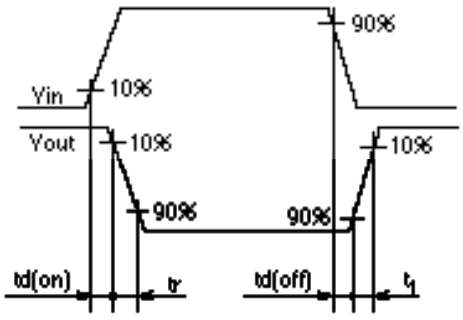
$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$

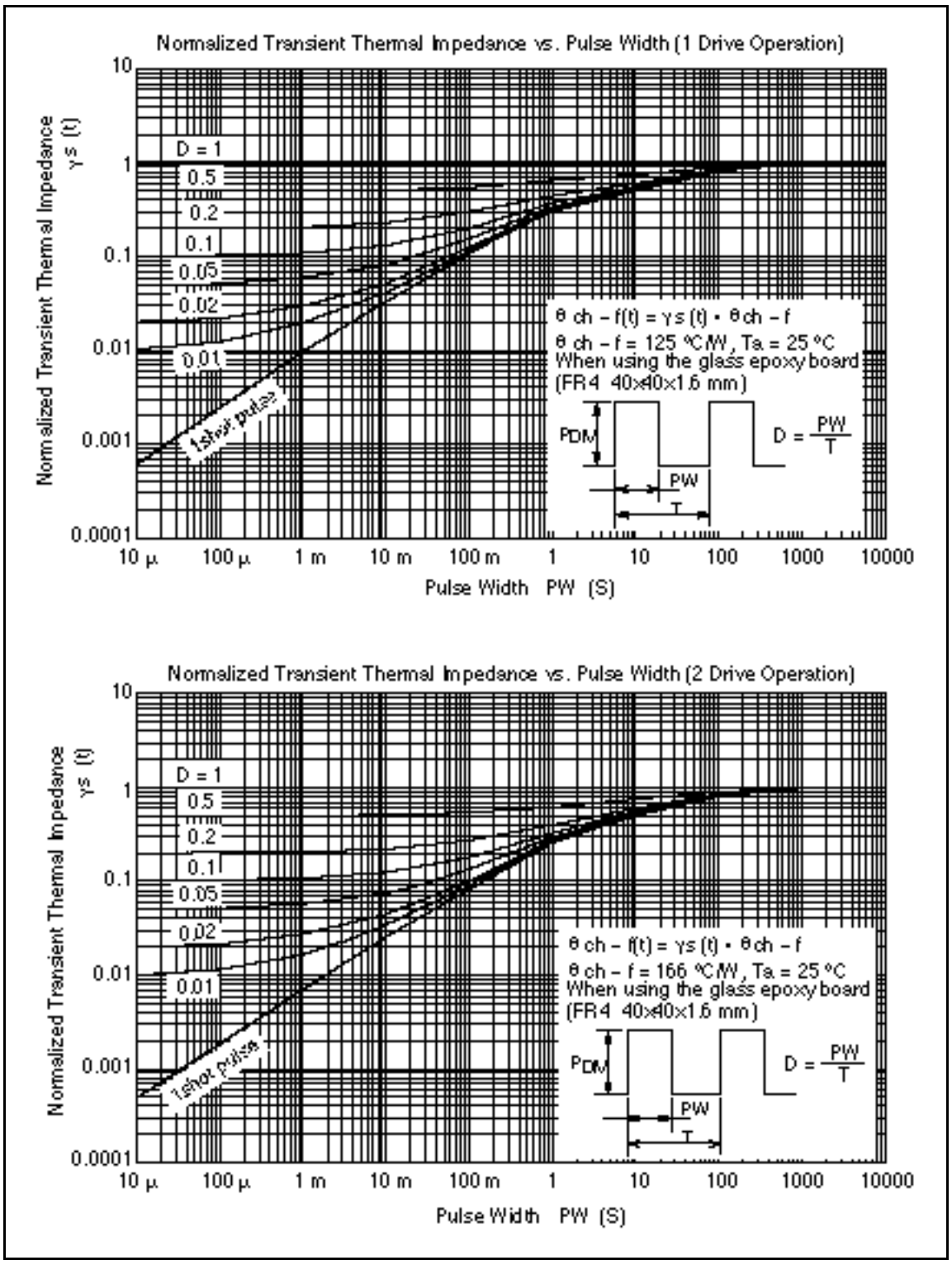


Switching Time Test Circuit



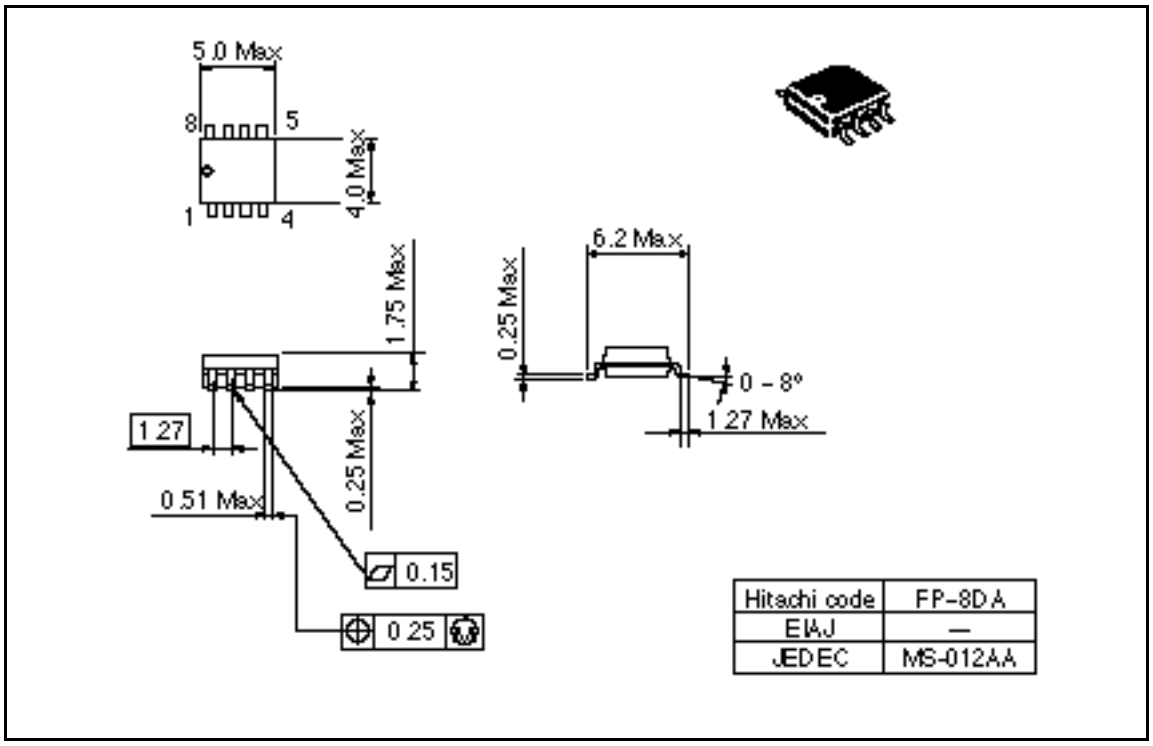
Switching Time Waveform




Normalized Transient Thermal Impedance vs. Pulse Width (1 Drive Operation)
Normalized Transient Thermal Impedance γs (t)
10
1
0.1
0.01
0.001
0.0001
D = 1
0.5
0.2
0.1
0.05
0.02
0.01
1shot pulse
θ ch – f(t) = γs (t) • θ ch – f
θ ch – f = 125 °C/W, Ta = 25 °C
When using the glass epoxy board
(FR4 40×40×1.6 mm)
PDM
PW
T
D = PW/T
10 µ
100 µ
1 m
10 m
100 m
1
10
100
1000
10000
Pulse Width PW (S)
Normalized Transient Thermal Impedance vs. Pulse Width (2 Drive Operation)
Normalized Transient Thermal Impedance γs (t)
10
1
0.1
0.01
0.001
0.0001
D = 1
0.5
0.2
0.1
0.05
0.02
0.01
1shot pulse
θ ch – f(t) = γs (t) • θ ch – f
θ ch – f = 166 °C/W, Ta = 25 °C
When using the glass epoxy board
(FR4 40×40×1.6 mm)
PDM
PW
T
D = PW/T
10 µ
100 µ
1 m
10 m
100 m
1
10
100
1000
10000
Pulse Width PW (S)

Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1897
Tel: c1s (800) 285-1601
Fax: c1s (303) 297-0447

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: c49s (89) 9 9180-0
Fax: c49s (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: c44s (1628) 585000
Fax: c44s (1628) 778322

Hitachi Asia Pte Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: c886s (2) 2718-3666
Fax: c886s (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: c852s (2) 735 9218
Fax: c852s (2) 730 0281
Telex: 40815 HITECHX